

**SP1100EC** 

**ROHS** 

### **Description**

P Series solid state protection thyristor protect telecommunications equipment such as modems, line cards, fax machines, and other CPE.

P Series solid state protection devices are used to enable equipment to meet various regulatory requirements including GR 1089, ITU K. 20, K. 21 and K. 45, IEC 60950, UL 60950, and TIA-968 (formerly known as FCC Part 68).

### **Electrical Parameters**

Compared to surge suppression using other technologies, P Series devices offer absolute surge protection regardless of the surge current available and the rate of applied voltage (dv/dt). P Series devices:

- · Cannot be damaged by voltage
- Eliminate hysteresis and heat dissipation typically found with clamping devices
- Eliminate voltage overshoot caused by fast-rising transients
- Are non-degenerative
- Will not fatigu
- Have low capacitance, making them ideal for high-speed transmission equipment

### **Electrical Parameters**

Parameter	r Definition	+I
<b>C</b> 0	Off-state Capacitance — typical capacitance	<b>A</b> .
	measured in off state	
di/dt	Rate of Rise of Current — maximum rated value of	Ιτ
	the acceptable rate of rise in current over time	
Is	Switching Current — maximum current required to	
	switch to on state	Is
${f I}$ DRM	Leakage Current — maximum peak off-state current	IH
	measured at VDRM	
${f I}_{\sf H}$	Holding Current — minimum current required to	
	maintain on state	I DRM
${f I}$ PP	Peak Pulse Current — maximum rated peak impulse -	+V
	Current	V <sub>T</sub> V <sub>DRM</sub> V <sub>S</sub>
IT	On-state Current — maximum rated continuous	
	on-state current	
<b>I</b> TSM	Peak One-cycle Surge Current — maximum rated	
	one-cycle AC current	
<b>V</b> s	Switching Voltage — maximum voltage prior to	1
	switching to on state	
<b>V</b> DRM	Peak Off-state Voltage — maximum voltage that can	
	be applied while maintaining off state	
<b>V</b> F	On-state Forward Voltage — maximum forward	
	voltage measured at rated on-state current	
<b>V</b> T	On-state Voltage — maximum voltage measured at	1 ↓
	Rated on-state current	- <b>I</b>



Over-voltage	r	SP1100EC					ROHS		
Electrical Cha	aracterist	cics							
Part	Vdrm	Vs	$V_{T}$	Idrm	Is	Iτ	Ін	Co	
Number	Volts	Volts	Volts	μ Amps	mAmps	Amps	mAmps	pF	
SP1100EC	90	130	4	5	800	2. 2	150	55	

<sup>\*</sup> For surge ratings, see table below.

### Notes:

- All measurements are made at an ambient temperature of 25℃. IPP applies to -40℃ through +85℃ temperature range.
- $\bullet$  Off-state capacitance (Co) is measured at 1 MHz with a 2 V bias and is typical value.

### Surge Ratings

Series	Ipp 2/10 µs Amps	Ipp 8/20 µs Amps	Ipp 10/160 µs Amps	Ipp 10/560 µs Amps	Ipp 10/1000 µs Amps	Itsm 60 Hz Amps	di/dt Amps/µs
С	500	400	200	150	100	50	500

# Thermal Considerations

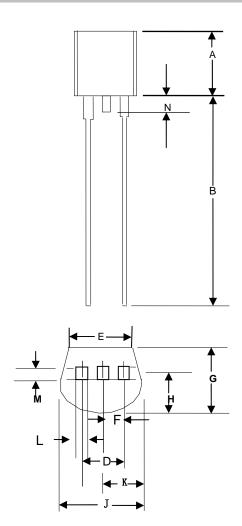
Package T0-92	Symbol	Parameter	Value	Unit
	ТЈ	Operating Junction Temperature	-40 to +150	℃
41	Ts	Storage Temperature Range	-40 to +150	°C
	R e ja	Junction to Ambient on printed circuit	90	°C/V



SP1100EC

ROHS

# Dimensions



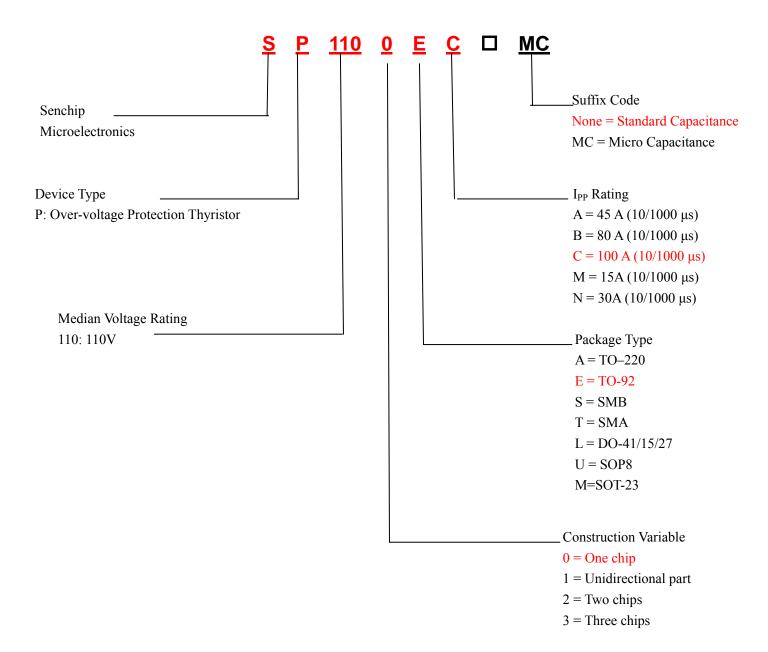
Dimension	In	ches	Millimeters		
	MIN	MIN	MIN	MIN	
A	0. 176	0. 196	4. 47	4. 98	
В	0. 5		12. 7		
D	0. 095	0. 105	2. 14	2. 67	
E	0. 15		3. 81		
F	0. 046	0. 054	1. 16	1. 37	
G	0. 135	0. 145	3. 43	3. 68	
Н	0. 088	0. 096	2. 23	2. 44	
J	0. 176	0. 186	4. 47	4. 73	
K	0. 088	0. 096	2. 23	2. 44	
L	0. 013	0. 019	0. 33	0. 48	
M	0. 013	0. 017	0. 33	0. 43	
N		0.06		1. 52	



**SP1100EC** 

ROHS

Description of Part Number

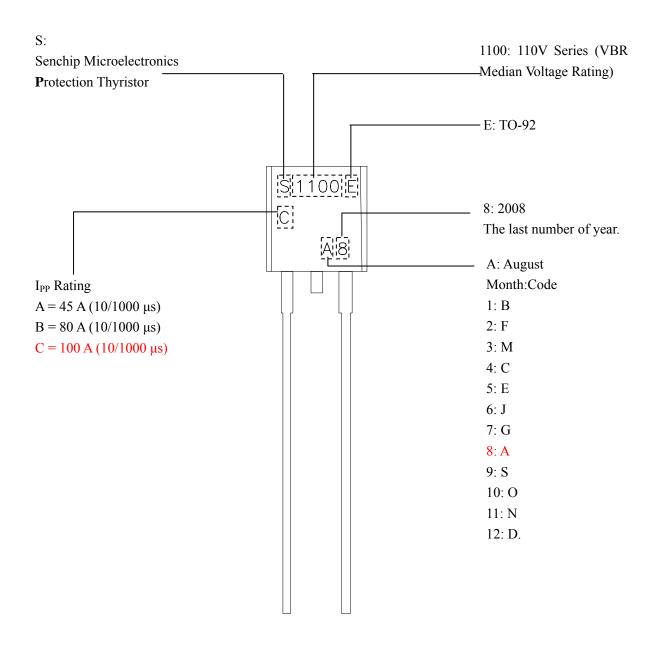




# **SP1100EC**

**ROHS** 

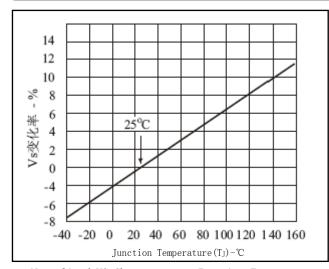
# Description of Marking



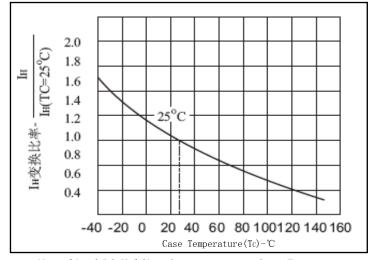


# Over-voltage Protection Thyristor Summary of Packing Options Package Type Description Packing Quantity T0-92 EA, EB, EC Bulk Pack SP1100EC ROHS AND Packing Quantity Standard N/A

## Thermal Derating Curves



Normalized VS Change versus Junction Temperature



Normalized DC Holding Current versus Case Temperature

